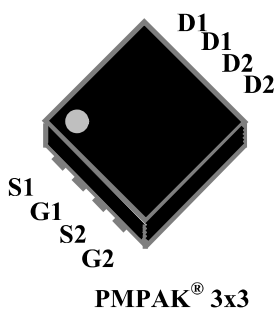


AP4822QD
N-Channel Power MOSFET

- ▼ Lower Gate Charge
- ▼ Simple Drive Requirement
- ▼ Fast Switching Characteristic
- ▼ RoHS Compliant & Halogen-Free

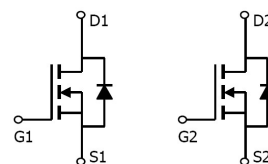


BV_{DSS}	30V
$R_{DS(ON)}$	15m Ω
I_D	8A

Description

AP4822QD series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The DFN3*3 package is widely preferred for all commercial-industrial surface mount applications using infrared reflow technique and suited for voltage conversion or switch applications.


Absolute Maximum Ratings@ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ\text{C}$	Drain Current, $V_{GS} @ 10V^3$	8	A
$I_D@T_A=70^\circ\text{C}$	Drain Current, $V_{GS} @ 10V^3$	5	A
I_{DM}	Pulsed Drain Current ¹	30	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation	2.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient ³	50	$^\circ\text{C}/\text{W}$

N-Channel Power MOSFET

Electrical Characteristics@ $T_j=25^{\circ}\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=8A$		15	20	$m\Omega$
		$V_{GS}=4.5V, I_D=6A$		28	36	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1	-	2.5	V
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=8A$		15		S
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=30V, V_{GS}=0V$	-	-	10	μA
I_{GSS}	Gate-Source Leakage	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Q_g	Total Gate Charge	$I_D=8A$		4.1		nC
Q_{gs}	Gate-Source Charge	$V_{DS}=15V$	-	1.1	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{GS}=4.5V$	-	2.5	-	nC
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=15V$	-	8	-	ns
t_r	Rise Time	$I_D=1A$	-	7	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega, V_{GS}=10V$	-	15	-	ns
t_f	Fall Time	$R_D=15\Omega$	-	5	-	ns
C_{iss}	Input Capacitance	$V_{GS}=0V$	-	350	420	pF
C_{oss}	Output Capacitance	$V_{DS}=25V$	-	55	-	pF
C_{rss}	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	35	-	pF
R_g	Gate Resistance	$f=1.0\text{MHz}$	-	3.2	-	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ²	$I_S=1.1A, V_{GS}=0V$	-	-	1.0	V
t_{rr}	Reverse Recovery Time	$I_S=8A, V_{GS}=0V,$	-	15	-	ns
Q_{rr}	Reverse Recovery Charge	$dI/dt=100A/\mu s$	-	14	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in² copper pad of FR4 board, $t \leq 10\text{sec}$; $125^{\circ}\text{C}/\text{W}$ when mounted on Min. copper pad.

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

APEC RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN.

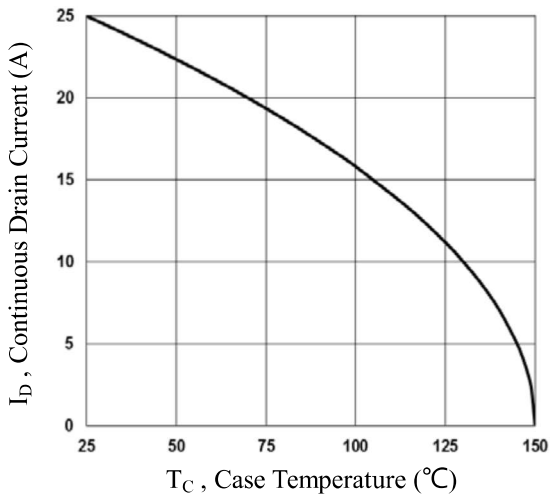


Fig.1 Continuous Drain Current vs. T_c

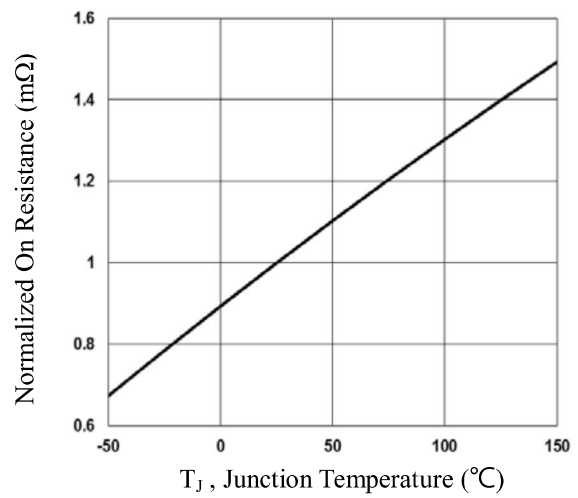


Fig.2 Normalized R_{DS(on)} vs. T_J

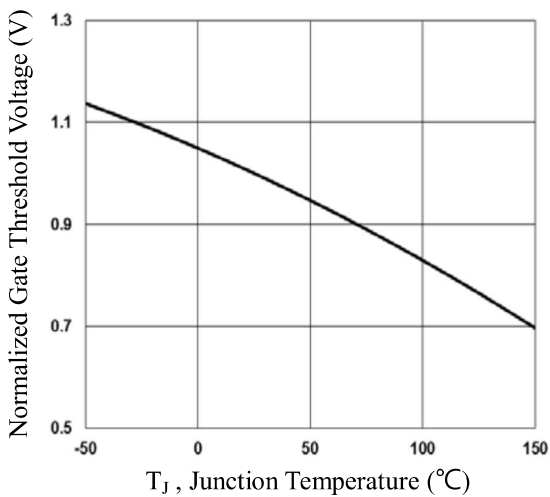


Fig.3 Normalized V_{th} vs. T_J

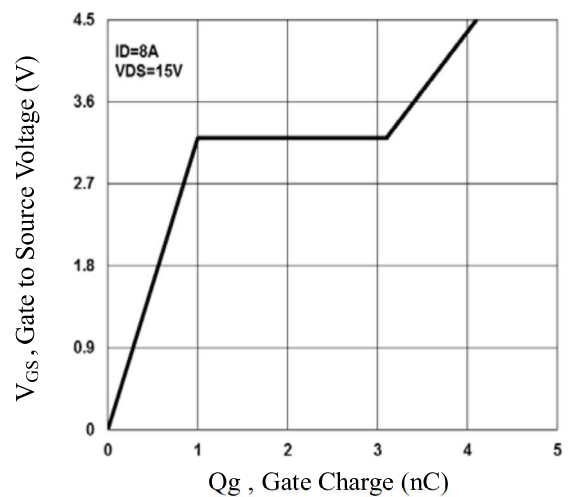


Fig.4 Gate Charge Waveform

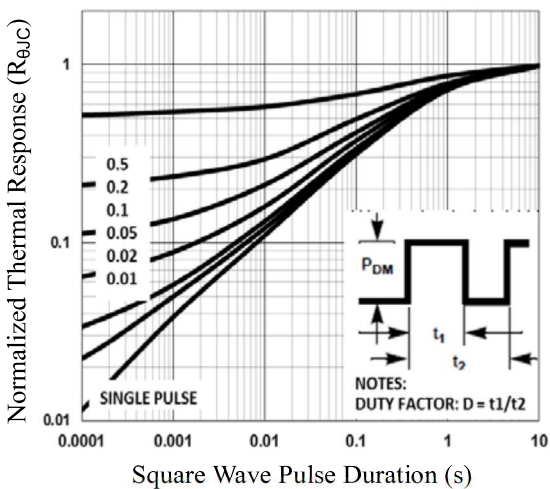


Fig.5 Normalized Transient Response

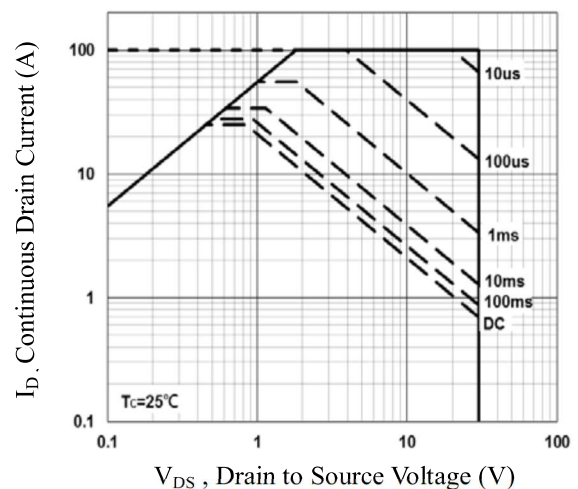


Fig.6 Maximum Safe Operation Area

AP4822QD

N-Channel Power MOSFET

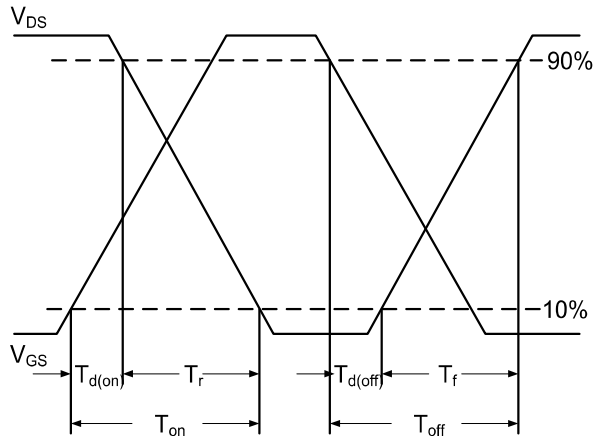


Fig.7 Switching Time Waveform

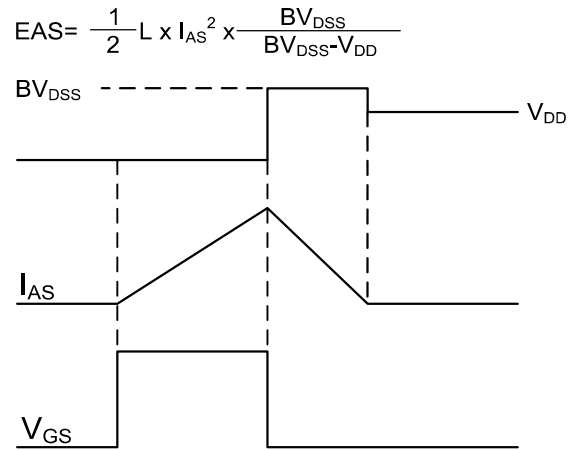


Fig.8 EAS Waveform